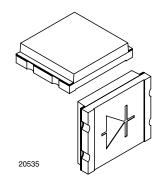


Vishay Semiconductors

Silicon PIN Photodiode, RoHS Compliant, Released for Lead (Pb)-free Solder Process, AEC-Q101 Released

Description

TEMD5110X01 is a high speed and high sensitive PIN photodiode. It is a miniature Surface Mount Device (SMD) including the chip with a 7.5 mm² sensitive area and an infrared bandpass filter matched to IR Emitters operating at wavelength 870 nm or 950 nm.



Features

- Product designed and qualified acc. AEC-Q101 for the automotive market
- Large radiant sensitive area:
 A = 7.5 mm²
- Wide angle of half sensitivity ϕ = ± 65 $^{\circ}$
- High photo sensitivity
- Fast response times
- Small junction capacitance
- Plastic package with IR filter: $\lambda = 870...950$ nm
- Floor life: 72 h, MSL 4, acc. J-STD-20
- Lead (Pb)-free component
- Component in accordance to ELV 2000/53/EC, RoHS 2002/95/EC and WEEE 2002/96/EC

Absolute Maximum Ratings

$T_{amb} = 25 \ ^{\circ}C$, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Reverse voltage		V _R	60	V
Power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	P _V	215	mW
Junction temperature		Тj	100	°C
Operating temperature range		T _{amb}	- 40 to + 100	°C
Storage temperature range		T _{stg}	- 40 to + 100	°C
Soldering temperature	In accordance with fig. 8	T _{sd}	260	°C
Thermal resistance junction/ ambient		R _{thJA}	350	K/W





- Automotive sensors
- Infrared detectors
- High speed photo detectors

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Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Forward voltage	I _F = 50 mA	V _F		1	1.3	V
Breakdown voltage	$I_{R} = 100 \ \mu A, \ E = 0$	V _(BR)	60			V
Reverse dark current	$V_{R} = 10 V, E = 0$	I _{ro}		2	30	nA
Diode capacitance	V _R = 0 V, f = 1 MHz, E = 0	CD		70		pF
	$V_{R} = 3 V$, f = 1 MHz, E = 0	CD		25	40	pF

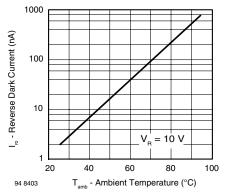
Optical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Тур.	Max	Unit
Open circuit voltage	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of V_{o}	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	ΤΚ _{Vo}		- 2.6		mV/K
Short circuit current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	I _k		50		μΑ
Temperature coefficient of I_k	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$	ΤΚ _{Ik}		0.1		%/K
Reverse light current	$E_e = 1 \text{ mW/cm}^2$, $\lambda = 950 \text{ nm}$, $V_R = 5 \text{ V}$	I _{ra}	45	55		μΑ
Angle of half sensitivity		φ		± 65		deg
Wavelength of peak sensitivity		λ _p		940		nm
Range of spectral bandwidth		λ _{0.5}		790 to 1050		nm
Noise equivalent power	V_R = 10 V, λ = 950 nm	NEP		4 x 10 ⁻¹⁴		W/√ Hz
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t _r		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega, \lambda = 820 \text{ nm}$	t _f		100		ns

Typical Characteristics

 $T_{amb} = 25 \text{ °C}$, unless otherwise specified





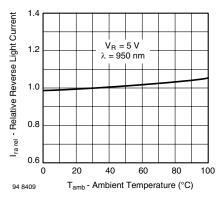


Figure 2. Relative Reverse Light Current vs. Ambient Temperature



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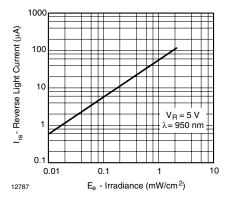


Figure 3. Reverse Light Current vs. Irradiance

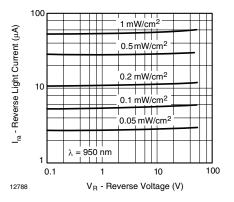


Figure 4. Reverse Light Current vs. Reverse Voltage

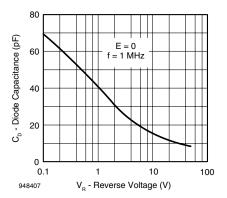


Figure 5. Diode Capacitance vs. Reverse Voltage

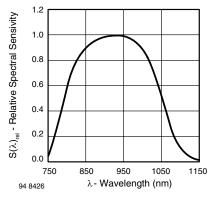


Figure 6. Relative Spectral Sensitivity vs. Wavelength

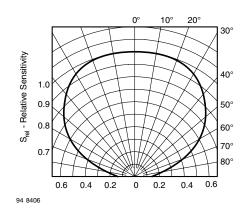
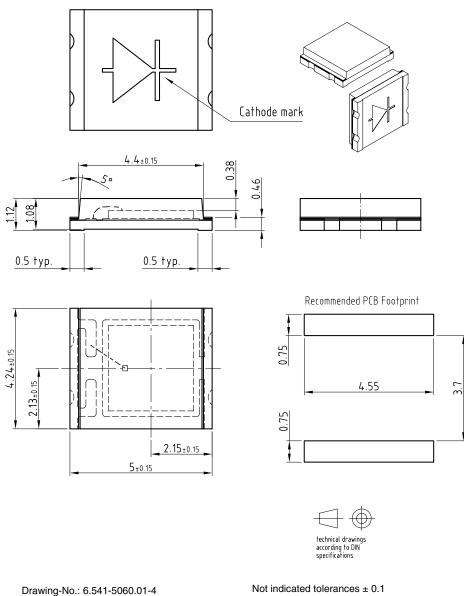


Figure 7. Relative Radiant Sensitivity vs. Angular Displacement

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Package Dimensions in millimeters





Issue: 2; 26.04.07 20536

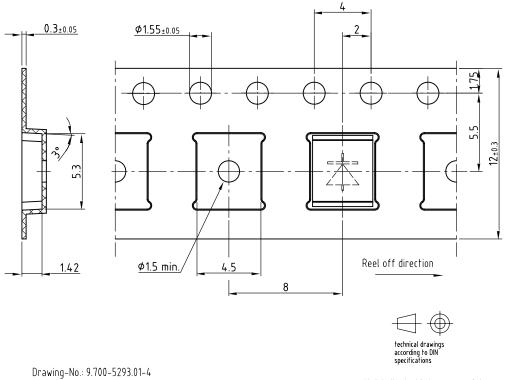
Minimum order quantity (MOQ): 1500 pcs (1 reel)

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Taping Dimensions in millimeters



Drawing-No.: 9.700-5293.01-Issue: 1; 03.12.04 20537

Not indicated tolerances ±0.1

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Reflow Solder Profiles

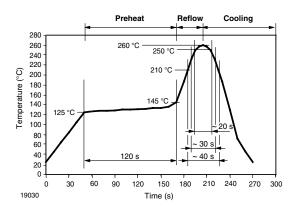


Figure 8. Lead (Pb)-free (Sn) Reflow Solder Profile

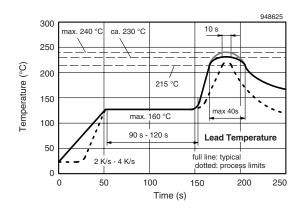


Figure 9. Lead Tin (SnPb) Reflow Solder Profile

Drypack

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

Floor Life

Floor life (time between soldering and removing from MBB) must not exceed the time indicated in J-STD-020. TEMD5110 is released for: Moisture Sensitivity Level 4, according to JEDEC, J-STD-020 Floor Life: 72 h Conditions: $T_{amb} < 30$ °C, RH < 60 %

Drying

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or Label. Devices taped on reel dry using recommended conditions 192 h at 40 °C (+ 5 °C), RH < 5 % or 96 h at 60 °C (+ 5 °C), RH < 5 %.



Vishay Semiconductors

Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



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